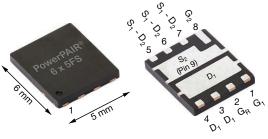
## SiZF640DT

www.vishay.com

**Vishay Siliconix** 

## Symmetric Dual N-Channel 40 V (D-S) MOSFET





Top View

Bottom View

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.00137			
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.00240			
Q <sub>g</sub> typ. (nC)	30			
I <sub>D</sub> (A) <sup>a</sup>	159			
Configuration	Dual			

#### **FEATURES**

- TrenchFET<sup>®</sup> Gen IV power MOSFET
- 100 %  $R_{\alpha}$  and UIS tested
- Symmetric dual N-channel
- · Flip chip technology optimal thermal design
- · High side and low side MOSFETs form optimized combination for 50 % duty cycle
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

Buck-boost

rectification

 Telecom DC/DC Motor drive control

- N-Channel 1 MOSFET G Half-bridge synchronous
  - N-Channel 2 MOSFET

ORDERING INFORMATION			
Package	PowerPAIR 6 x 5FS		
Lead (Pb)-free and halogen-free	SiZF640DT-T1-GE3		

PARAMETER Drain-source voltage Gate-source voltage		SYMBOL	LIMIT	UNIT	
		V <sub>DS</sub>	40	V	
		V <sub>GS</sub>	+20, -16		
	T <sub>C</sub> = 25 °C		159		
Or attack during a summer (T 150 °C)	T <sub>C</sub> = 70 °C		127	_	
Continuous drain current ( $T_J = 150 \ ^{\circ}C$ )	T <sub>A</sub> = 25 °C	I <sub>D</sub>	41 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		33 <sup>b, c</sup>		
Pulsed drain current (t = 100 µs)		I <sub>DM</sub>	300	— A	
	T <sub>C</sub> = 25 °C		57		
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	3.8 <sup>b, c</sup>		
Single pulse avalanche current L = 0.1 mH   Single pulse avalanche energy L = 0.1 mH		I <sub>AS</sub>	40		
		E <sub>AS</sub>	80	mJ	
	T <sub>C</sub> = 25 °C		62.5		
Maximum power dissipation	T <sub>C</sub> = 70 °C		40	w	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	4.2 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		2.7 <sup>b, c</sup>		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	**	
Soldering recommendations (peak temperature) d, e		3	260		

#### Notes

a.  $T_C = 25 \ ^{\circ}C$ 

b. Surface mounted on 1" x 1" FR4 board

c. t = 10 s

See solder profile (www.vishav.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not d. plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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HALOGEN

FREE

S₁-D₂



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THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYP.	MAX.	UNIT	
Maximum junction-to-ambient a, b	$t \le 10 s$	R <sub>thJA</sub>	24	30	°C/W	
Maximum junction-to-case (source)	Steady state	R <sub>thJC</sub>	1.6	2.0	0/10	

Notes

a. Surface mounted on 1" x 1" FR4 board

b. Maximum under steady state conditions is 60 °C/W for channel-1 and channel-2

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	40	-	-	V	
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10 \text{ mA}$		25.3	-	m\//%C	
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA	-	-5.5	-	mV/°C	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1	-	2.4	V	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = +20 V, -16 V$	-	-	± 100	nA	
Zero gate voltage drain current		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μΑ	
	IDSS	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	-	-	10		
<b>D</b> · · · · · · · · · · · · · · · · · · ·		$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	-	0.0010	0.00137	- Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A	-	0.0016	0.00240		
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 45 A	-	175	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	5750	-	pF	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	960	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	55	-		
<b>-</b>		$V_{DS} = 20 V, V_{GS} = 10 V, I_D = 15 A$	-	69	106	nC	
Total gate charge	Qg		-	30	45		
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	21	-		
Gate-drain charge	Q <sub>gd</sub>		-	1.5	-		
Output charge	Q <sub>oss</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	46	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.7	3.4	Ω	
Turn-on delay time	t <sub>d(on)</sub>		-	18	40		
Rise time	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega, \text{ I}_{D} \cong 10 \text{ A},$	-	45	90		
Turn-off delay time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	45	90		
Fall time	t <sub>f</sub>		-	6	12		
Turn-on delay time	t <sub>d(on)</sub>		-	50	100	ns	
Rise time	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega, \text{ I}_{D} \cong 10 \text{ A},$	-	115	230	-	
Turn-off delay time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	40	80		
Fall time	t <sub>f</sub>		-	10	20		
Drain-Source Body Diode Characterist	cs						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	57	•	
Pulse diode forward current	I <sub>SM</sub>	-		-	300	A	
Body diode voltage	V <sub>SD</sub>	$I_{\rm S}$ = 10 A, $V_{\rm GS}$ = 0 V	-	0.75	1.1	V	
Body diode reverse recovery time	t <sub>rr</sub>		-	40	80	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>		-	36	75	nC	
Reverse recovery fall time	t <sub>a</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	25	-		
Reverse recovery rise time	t <sub>b</sub>		-	15	-	ns	

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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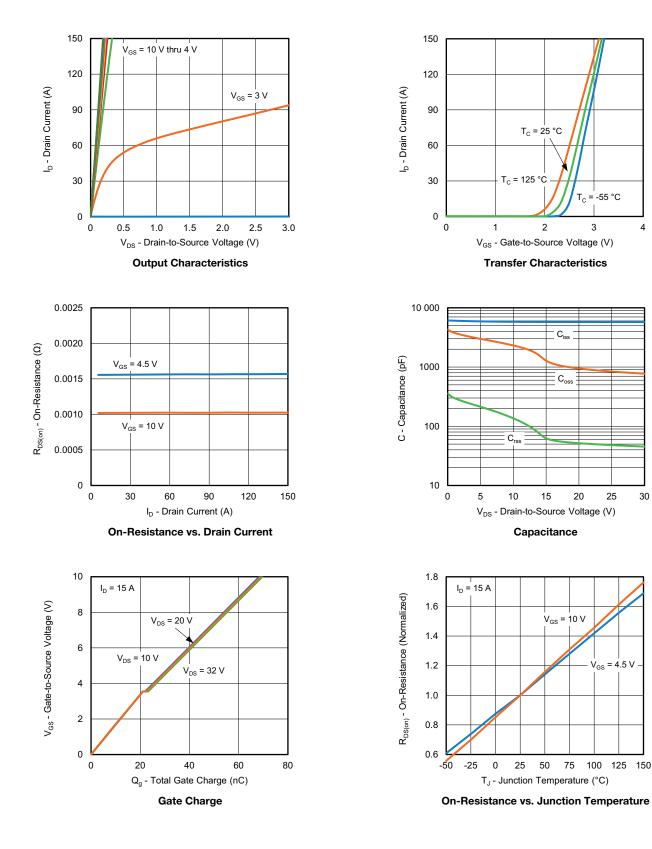
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



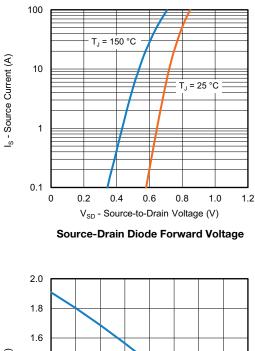
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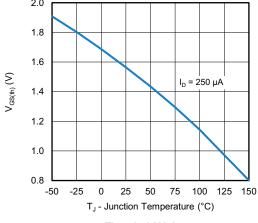
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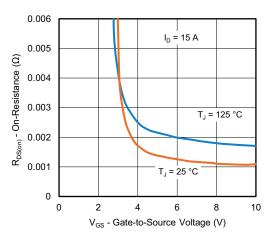
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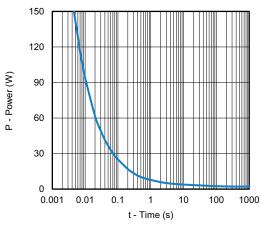




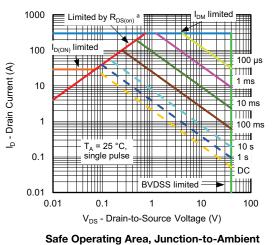




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Note

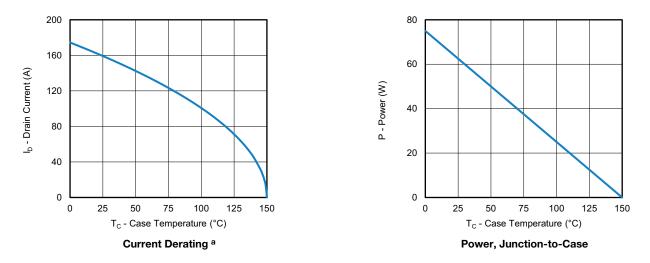
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



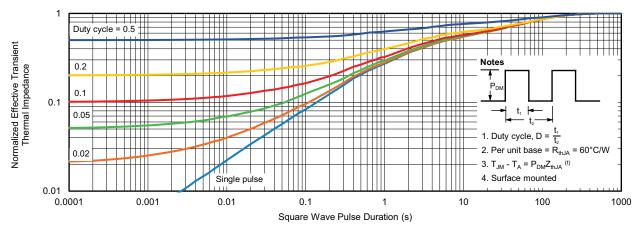
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

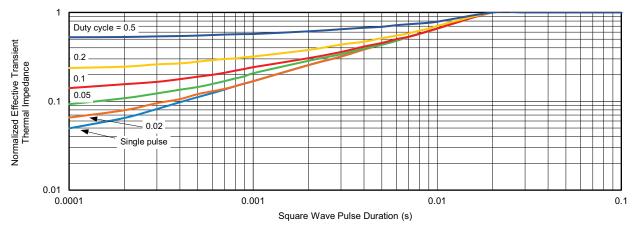


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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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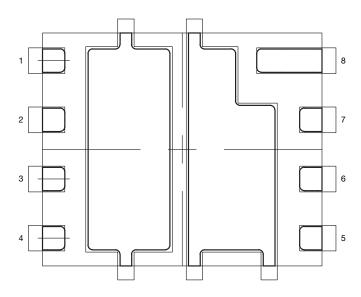
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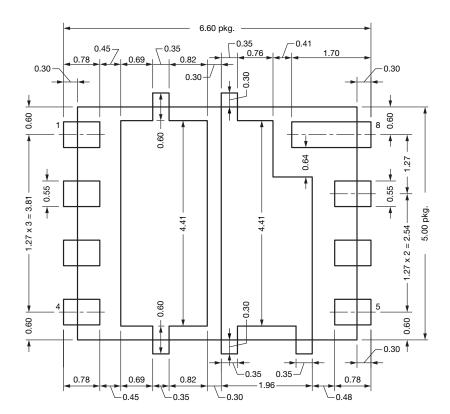
### **PAD** Pattern



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### Recommended Land Pattern PowerPAIR<sup>®</sup> 6 x 5 FS and PowerPAIR<sup>®</sup> 6 x 5 FSW





#### Note

• Dimensions in mm

T24-0311-Rev. A, 09-Sep-2024 DWG: 3030

Revision: 09-Sep-2024

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